



11/3/2010

**PRODUCT RELIABILITY REPORT
FOR**

DS1804, Rev B2

Maxim Integrated Products

**4401 South Beltwood Parkway
Dallas, TX 75244-3292**

Prepared by:

**Don Lipps
Manager, Reliability Engineering
Maxim Integrated Products
4401 South Beltwood Pkwy.
Dallas, TX 75244-3292
Email: don.lipps@maxim-ic.com
ph: 972-371-3739**

Conclusion:

The following qualification successfully meets the quality and reliability standards required of all Maxim products:

DS1804, Rev B2

In addition, Maxim's continuous reliability monitor program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards. The current status of the reliability monitor program can be viewed at <http://www.maxim-ic.com/TechSupport/dsreliability.html>.

Device Description:

A description of this device can be found in the product data sheet. You can find the product data sheet at http://dbserv.maxim-ic.com/l_datasheet3.cfm.

Reliability Derating:

The Arrhenius model will be used to determine the acceleration factor for failure mechanisms that are temperature accelerated.

$$AfT = \exp((Ea/k) * (1/Tu - 1/Ts)) = tu/ts$$

AfT = Acceleration factor due to Temperature
tu = Time at use temperature (e.g. 55°C)
ts = Time at stress temperature (e.g. 125°C)
k = Boltzmann's Constant (8.617 x 10⁻⁵ eV/°K)
Tu = Temperature at Use (°K)
Ts = Temperature at Stress (°K)
Ea = Activation Energy (e.g. 0.7 ev)

The activation energy of the failure mechanism is derived from either internal studies or industry accepted standards, or activation energy of 0.7ev will be used whenever actual failure mechanisms or their activation energies are unknown. All deratings will be done from the stress ambient temperature to the use ambient temperature.

An exponential model will be used to determine the acceleration factor for failure mechanisms, which are voltage accelerated.

$$AfV = \exp(B * (Vs - Vu))$$

AfV = Acceleration factor due to Voltage
Vs = Stress Voltage (e.g. 7.0 volts)
Vu = Maximum Operating Voltage (e.g. 5.5 volts)
B = Constant related to failure mechanism type (e.g. 1.0, 2.4, 2.7, etc.)

The Constant, B, related to the failure mechanism is derived from either internal studies or industry accepted standards, or a B of 1.0 will be used whenever actual failure mechanisms or their B are unknown. All deratings will be done from the stress voltage to the maximum operating voltage. Failure rate data from the operating life test is reported using a Chi-Squared statistical model at the 60% or 90% confidence level (Cf).

The failure rate, Fr, is related to the acceleration during life test by:

$$Fr = X / (ts * AfV * AfT * N * 2)$$

X = Chi-Sq statistical upper limit
N = Life test sample size

Failure Rates are reported in FITs (Failures in Time) or MTTF (Mean Time To Failure). The FIT rate is related to MTTF by:

$$MTTF = 1/Fr$$

NOTE: MTTF is frequently used interchangeably with MTBF.

The calculated failure rate for this device/process is:

FAILURE RATE: **MTTF (YRS):** **26795** **FITS:** **4.3**
DEVICE HOURS: **474677145** **FAILS:** **1**

Only data from Operating Life or similar stresses are used for this calculation.

The parameters used to calculate this failure rate are as follows:

Cf: 60% **Ea: 0.7** **B: 0** **Tu: 25 °C** **Vu: 5.5 Volts**

The reliability data follows. At the start of this data is the device information. The next section is the detailed reliability data for each stress. The reliability data section includes the latest data available and may contain some generic data. **Bold** Product Number denotes specific product data.

Device Information:

Process: SA E6W, 0.6um BiCMOS, 2 Poly, 2 Metal, EEPROM, 8 inch wafer
Passivation: TEOS Oxide-Nitride Passivation
Die Size: 68.110236 x 65.354331
Number of Transistors: 5414
Interconnect: Aluminum / 0.5% Copper
Gate Oxide Thickness: 150 Å

ESD HBM

DESCRIPTION	DATE	CODE/PRODUCT/LOT	CONDITION	READPOIN	QTY	FAILS	FA#
ESD SENSITIVITY	1021	DS1804	WD049849A JESD22-A114 HBM 500 VOLTS	1	PUL'S	3	0
ESD SENSITIVITY	1021	DS1804	WD049849A JESD22-A114 HBM 1000 VOLTS	1	PUL'S	3	0
ESD SENSITIVITY	1021	DS1804	WD049849A JESD22-A114 HBM 2000 VOLTS	1	PUL'S	3	0
ESD SENSITIVITY	1021	DS1804	WD049849A JESD22-A114 HBM 4000 VOLTS	1	PUL'S	3	3 No FA
ESD SENSITIVITY	1021	DS1804	WD049849A JESD22-A114 HBM 8000 VOLTS	1	PUL'S	3	3 No FA
Total:						6	

LATCH-UP

DESCRIPTION	DATE	CODE/PRODUCT/LOT	CONDITION	READPOIN	QTY	FAILS	FA#
LATCH-UP I	1021	DS1804	WD049849A JESD78A, I-TEST 25C 100mA			6	0
LATCH-UP V	1021	DS1804	WD049849A JESD78A, V-SUPPLY TEST 25C			6	0
Total:						0	

OPERATING LIFE

DESCRIPTION	DATE	CODE/PRODUCT/LOT	CONDITION	READPOIN	QTY	FAILS	FA#
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HIGH TEMP OP LIFE	0851	DS1859	WJ943223KA 125C, 5.5 VOLTS	1000 HRS	77	0
HIGH TEMP OP LIFE	0903	DS1859	WJ943224O 125C, 5.5 VOLTS	1000 HRS	77	0
HIGH TEMP OP LIFE	0903	DS1859	WJ942980M 125C, 5.5 VOLTS	1000 HRS	77	0
HIGH TEMP OP LIFE	0916	DS1859	WJ946557K 125C, 5.5 VOLTS	1000 HRS	77	0
HIGH TEMP OP LIFE	0916	DS1859	WJ946557K 125C, 5.5 VOLTS	408 HRS	80	0
HIGH TEMP OP LIFE	0921	DS1859	WJ946573A 125C, 5.5 VOLTS	1000 HRS	77	0
HIGH TEMP OP LIFE	0948	DS1856	WM049367A 125C, 5.5 VOLTS	1000 HRS	77	1 40023508
HIGH TEMP OP LIFE	1021	DS1804	WD049849A 125C, 5.5 VOLTS	192 HRS	45	0

Total: 1

FAILURE RATE: **MTTF (YRS):** **26795** **FITS:** **4.3**
DEVICE HOURS: **474677145** **FAILS:** **1**

40023508 - FA result showed gate oxide defect in an NMOS transistor.